

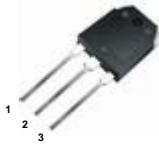
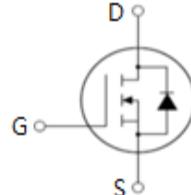
600V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

$BV_{DSS} = 600 \text{ V}$ $R_{DS(on)\text{ typ}} = 0.34 \Omega$ $I_D = 20 \text{ A}$	 1. Gate 2. Drain 3. Source	
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Device Marking and Package Information

Device	Package	Marking
HA20N60	TO-3P	HA20N60

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-3P	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	600	V
Continuous Drain Current	I_D	20	A
Pulsed Drain Current (note1)	I_{DM}	80	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	1350	mJ
Avalanche Current (note1)	I_{AR}	16	A
Repetitive Avalanche Energy (note1)	E_{AR}	90	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	120	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	C

Thermal Resistance

Parameter	Symbol	Value	Unit
		TO-3P	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.04	C/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	600	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 600\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 30\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 10\text{A}$	--	0.34	0.40	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	2978	--	pF
Output Capacitance	C_{oss}		--	291	--	
Reverse Transfer Capacitance	C_{rss}		--	40	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 480\text{V}, I_D = 20\text{A}, V_{\text{GS}} = 10\text{V}$	--	80	--	nC
Gate-Source Charge	Q_{gs}		--	12	--	
Gate-Drain Charge	Q_{gd}		--	34	--	
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{\text{DD}} = 250\text{V}, I_D = 20\text{A}, R_G = 25\Omega$	--	37	--	ns
Turn-on Rise Time	t_r		--	66	--	
Turn-off Delay Time	$t_{d(\text{off})}$		--	175	--	
Turn-off Fall Time	t_f		--	84	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	20	A
Pulsed Diode Forward Current	I_{SM}		--	--	80	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 20\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}} = 0\text{V}, I_S = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	450	--	ns
Reverse Recovery Charge	Q_{rr}		--	7.1	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 16\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

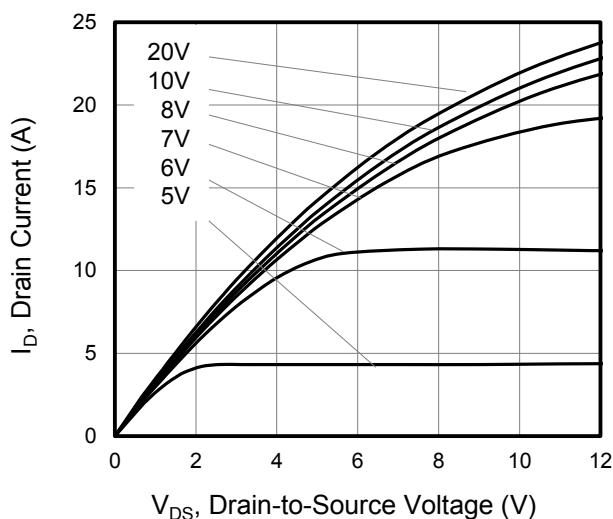


Figure 2. Body Diode Forward Voltage

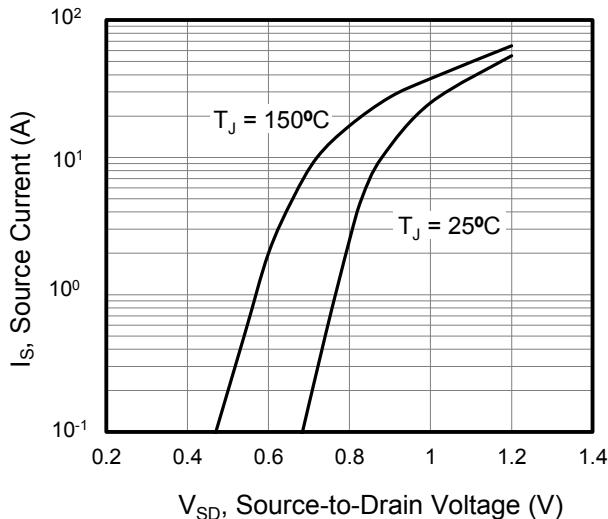


Figure 3. Drain Current vs. Temperature

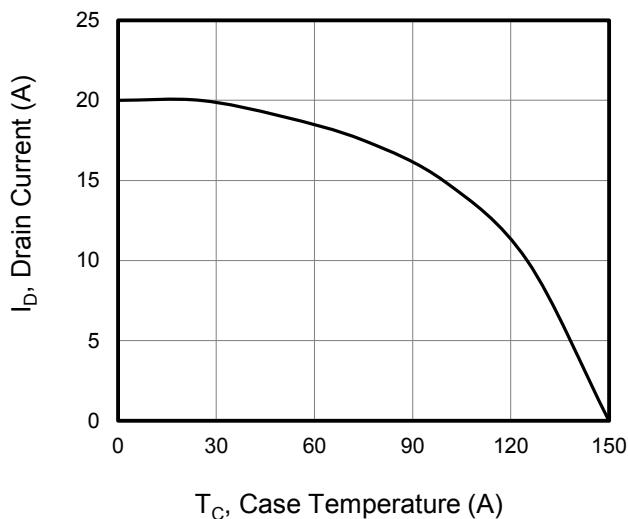


Figure 4. BV_{DSS} Variation vs. Temperature

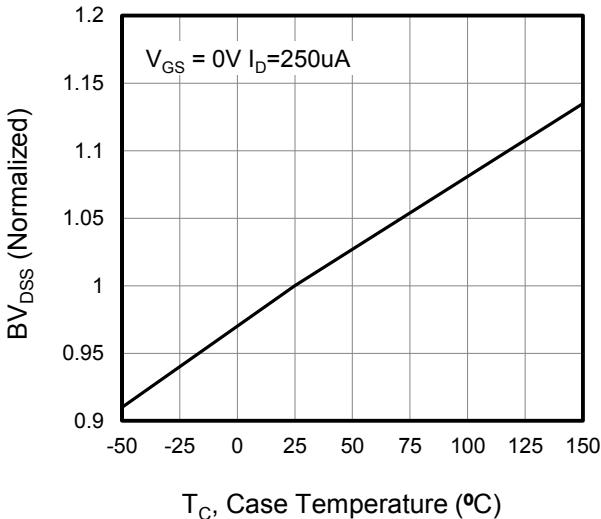


Figure 5. Transfer Characteristics

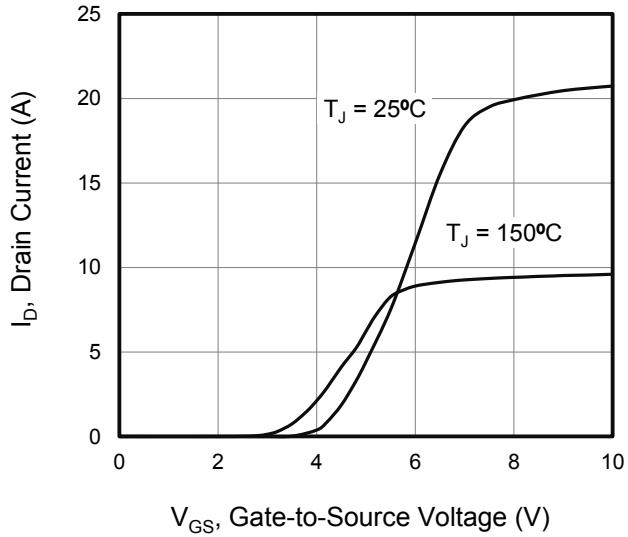
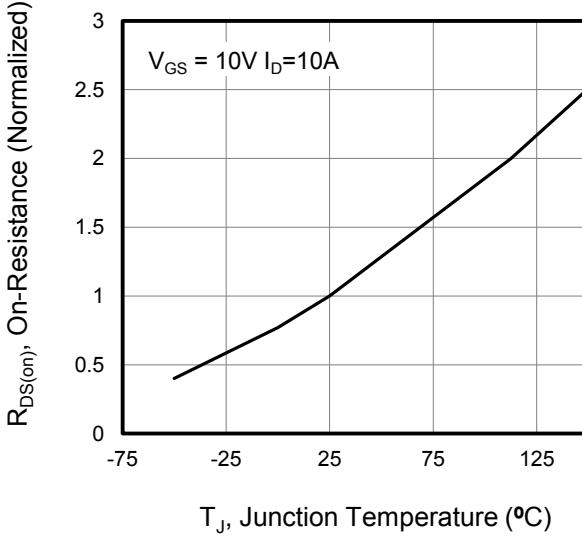


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

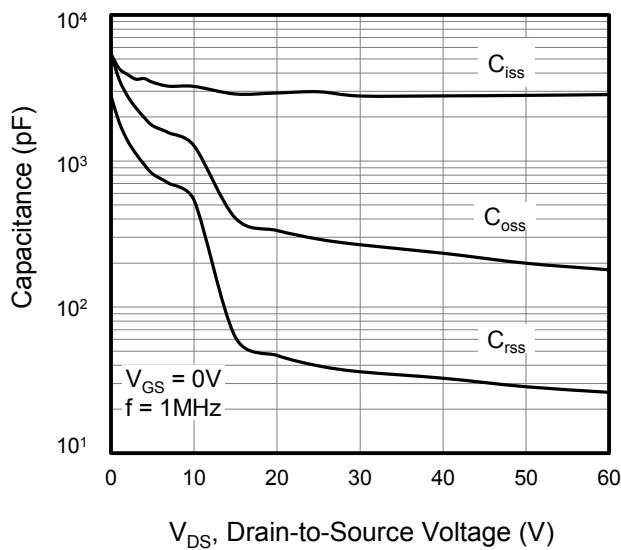


Figure 8. Gate Charge

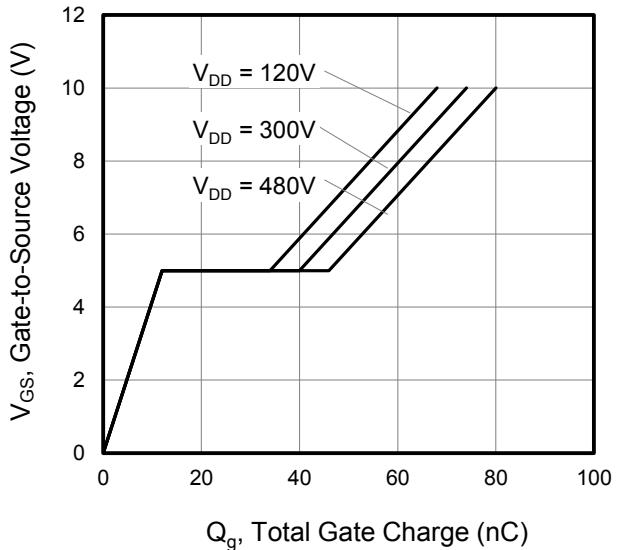


Figure 9. Transient Thermal Impedance

TO-220F

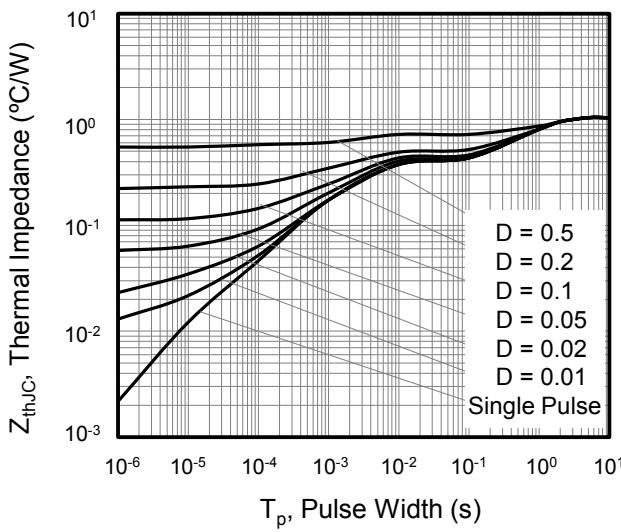


Figure A: Gate Charge Test Circuit and Waveform

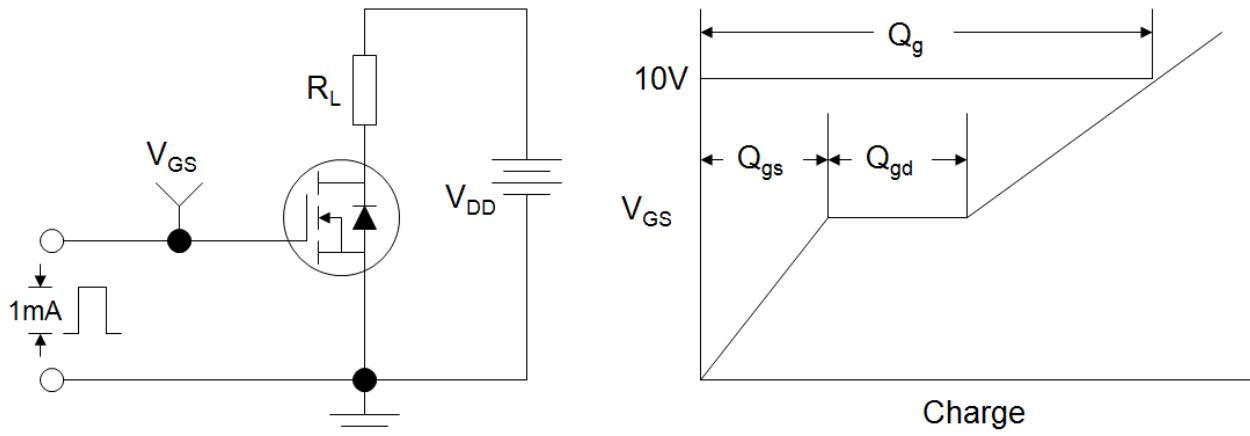


Figure B: Resistive Switching Test Circuit and Waveform

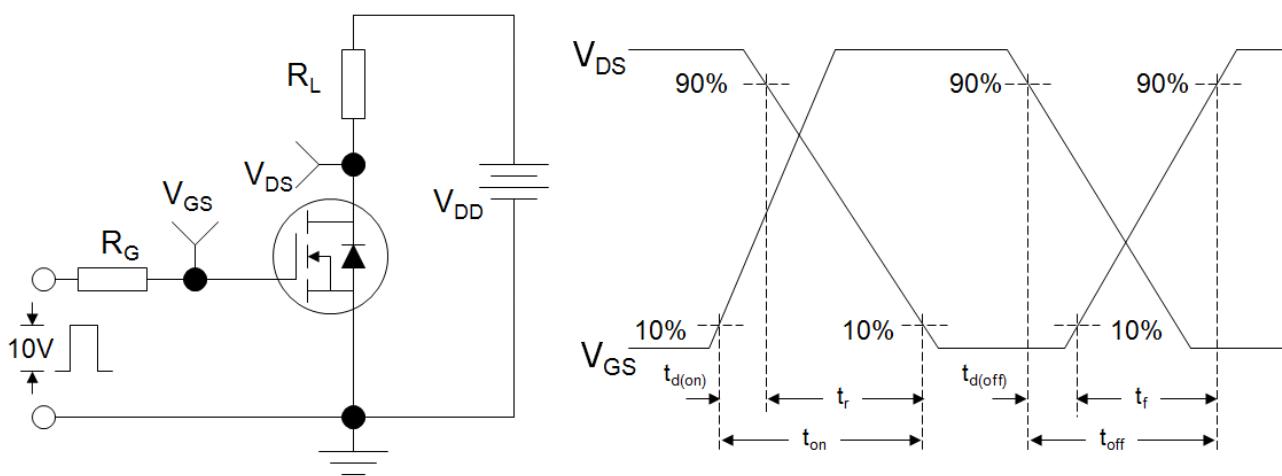
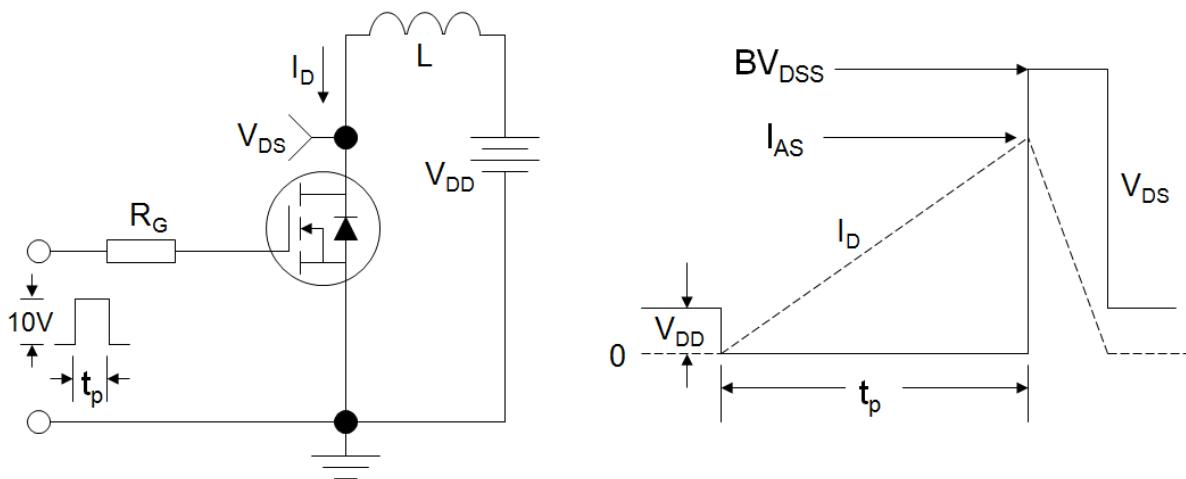


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-3P

